

### 6-BIT, 2:1, SINGLE-ENDED LVCMOS MULTIPLEXER

ICS83056I-01

# **General Description**



The ICS83056I-01 is a 6-bit, 2:1, Single-ended LVCMOS Multiplexer and a member of the HiPerClockS™ family of High Performance Clock Solutions from IDT. The ICS83056I-01 has two selectable single-ended LVCMOS clock inputs and

six single-ended LVCMOS clock outputs. The outputs have a  $V_{\rm DDO}$  which may be set at 3.3V, 2.5V, or 1.8V, making the device ideal for use in voltage translation applications. An output enable pin places the output in a high impedance state which may be useful for testing or debug. Possible applications include systems with up to 6 transceivers which need to be independently set for different rates. For example, a board may have six transceivers, each of which need to be independently configured for 1 Gigabit Ethernet or 1 Gigabit Fibre Channel rates. Another possible application may require the ports to be independently set for FEC (Forward Error Correction) or non-FEC rates. The device operates up to 250MHz and is packaged in a 20 TSSOP.

**Block Diagram** CLK0 Pulldow 0 CO CLK1 Pulldown SEL0 Pulldown 0 Ω1 1 SEL1 Pulldown 0 Ω2 SEL2 Pulldown 0 Q3 SEL3 Pulldown 0 SEL4 Pulldown 0 Q5 SEL5 Pulldown OE . Pullup

#### **Features**

- 6-Bit, 2:1 single-ended LVCMOS multiplexer
- Maximum output frequency: 250MHz
- Additive phase jitter, RMS at 155.52MHz (12kHz 20MHz): 0.18ps (typical)
- Operating supply modes:

Core/Output

 $V_{DD}/V_{DDO}$ 

3.3V/3.3V

3.3V/2.5V

3.3V/1.8V

2.5V/2.5V

2.5V/1.8V

- -40°C to 85°C ambient operating temperature
- Available in both standard (RoHS 5) and lead-free (RoHS 6) packages

# **Pin Assignment**

SEL5□	1	20	□SEL0
Q5□	2	19	□ Q0
$V_{DDO}$	3	18	□Vddo
GND□	4	17	□GND
Q4 🗆	5	16	□Q1
SEL4□	6	15	☐ SEL1
CLK1 ☐	7	14	□CLK0
$V_{DD}\square$	8	13	□0E
Q3 🗆	9	12	□Q2
SEL3□	10	11	☐ SEL2

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20-Lead TSSOP 6.50mm x 4.40mm x 0.925mm package body G Package Top View

IDT™ / ICS™ 2:1, SINGLE-ENDED LVCMOS MULTIPLEXER

ICS83056AGI-01 REV. A JANUARY 29, 2009

**Table 1. Pin Descriptions** 

Number	Name	•	Гуре	Description
1, 6 10, 11 15, 20	SEL5, SEL4, SEL3, SEL2, SEL1, SEL0	Input	Pulldown	Clock select inputs. See Table 3. LVCMOS / LVTTL interface levels.
2, 5, 9 12, 16, 19	Q5, Q4, Q3, Q2, Q1, Q0	Output		Single-ended clock output. LVCMOS/LVTTL interface levels.
3, 18	$V_{DDO}$	Power		Output supply pins.
4, 17	GND	Power		Power supply ground.
7, 14	CLK1, CLK0	Input	Pulldown	Single-ended clock inputs. LVCMOS/LVTTL interface levels.
8	$V_{DD}$	Power		Power supply pin.
13	OE	Input	Pullup	Output enable. When LOW, outputs are in a High impedance state. When HIGH, outputs are active. LVCMOS / LVTTL interface levels.

NOTE: Pullup and Pulldown refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

### **Table 2. Pin Characteristics**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance			4		pF
	5 5: 6 ::	$V_{DD} = V_{DDO} = 3.465V$		18		pF
C <sub>PD</sub>	Power Dissipation Capacitance (per output)	$V_{DD} = V_{DDO} = 2.625V$		19		pF
	(I. s. s. A. s. A.	$V_{DD} = V_{DDO} = 2V$	4 pF 18 pF	pF		
R <sub>PULLUP</sub>	Input Pullup Resistor			51		kΩ
R <sub>PULLDOWN</sub>	Input Pulldown Resistor			51		kΩ
C <sub>IN</sub> C <sub>PD</sub>		$V_{DDO} = 3.465V$		15		Ω
	Output Impedance	V <sub>DDO</sub> = 2.625V		17		Ω
		$V_{DDO} = 2V$		25		Ω

# **Function Tables**

**Table 3. Control Input Function Table** 

Control Inputs	Outputs
SELx	Qx
0	CLK0
1	CLK1

# **Absolute Maximum Ratings**

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V <sub>DD</sub>	4.6V
Inputs, V <sub>I</sub>	-0.5V to V <sub>DD</sub> + 0.5V
Outputs, V <sub>O</sub>	-0.5V to V <sub>DDO</sub> + 0.5V
Package Thermal Impedance, $\theta_{JA}$	91.1°C/W (0 mps)
Storage Temperature, T <sub>STG</sub>	-65°C to 150°C

### **DC Electrical Characteristics**

Table 4A. Power Supply DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $V_{DDO} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ , or  $1.8V \pm 0.2V$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Positive Supply Voltage		3.135	3.3	3.465	V
			3.135	3.3	3.465	V
$V_{DDO}$	Output Supply Voltage		2.375	2.5	2.625	V
			1.6	1.8	2.0	V
I <sub>DD</sub>	Power Supply Current				45	mA
I <sub>DDO</sub>	Output Supply Current	No Load			5	mA

Table 4B. Power Supply DC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $V_{DDO} = 2.5V \pm 5\%$  or  $1.8V \pm 0.2V$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Positive Supply Voltage		2.375	2.5	2.625	V
V	Outrot Complex Valtage		2.375	2.5	2.625	V
$V_{DDO}$	Output Supply Voltage		1.6	1.8	2.0	V
I <sub>DD</sub>	Power Supply Current				40	mA
I <sub>DDO</sub>	Output Supply Current	No Load			5	mA

Table 4C. LVCMOS/LVTTL DC Characteristics,  $T_A = -40 \,^{\circ} C$  to  $85 \,^{\circ} C$ 

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V	Innut Lligh Valta		V <sub>DD</sub> = 3.465V	2		V <sub>DD</sub> + 0.3	V
VIН	input High Volta	.ge	V <sub>DD</sub> = 2.625V	1.7		V <sub>DD</sub> + 0.3	V
V	Input Low Voltage	~~	V <sub>DD</sub> = 3.465V	-0.3		1.3	V
V IL	input Low Voltag	ye	V <sub>DD</sub> = 2.625V	-0.3		0.7	V
I <sub>IH</sub>	Input	CLK0, CLK1, SEL[0:5]	V <sub>DD</sub> = V <sub>IN</sub> = 3.465V or 2.625V			150	μA
	High Current	OE	$V_{DD} = 3.465V \qquad 2 \qquad V_{DD} \\ V_{DD} = 2.625V \qquad 1.7 \qquad V_{DD} \\ V_{DD} = 3.465V \qquad -0.3 \\ V_{DD} = 2.625V \qquad -0.3 \\ V_{DD} = 2.625V \qquad -0.3 \\ V_{DD} = 2.625V \qquad -0.3 \\ V_{DD} = V_{IN} = 3.465V \text{ or } 2.625V \\ V_{DD} = V_{IN} = 3.465V \text{ or } 2.625V \\ V_{DD} = 3.465V \text{ or } 2.625V \\ V_{DD} = 3.465V \text{ or } 2.625V, V_{IN} = 0V \\ V_{DD} = 3.465V \text{ or } 2.625V, V_{IN} = 0V \\ V_{DD} = 3.465V \text{ or } 2.625V, V_{IN} = 0V \\ V_{DD} = 3.3V \pm 5\%, I_{OH} = -24\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OH} = -12\text{mA} \\ V_{DD} = 3.3V \pm 5\%, I_{OL} = 24\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 24\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{OL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 12\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 2\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 2\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 2\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 2\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 2\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 2\text{mA} \\ V_{DD} = 2.5V \pm 5\%, I_{DL} = 2$	5	μΑ		
I <sub>II</sub>	Input	CLK0, CLK1, SEL[0:5]	V <sub>DD</sub> = 3.465V or 2.625V, V <sub>IN</sub> = 0V	-5			μA
V <sub>IH</sub> III V <sub>IL</sub> III III III IL III VOH	Low Current	OE	V <sub>DD</sub> = 3.465V or 2.625V, V <sub>IN</sub> = 0V	-150			μΑ
' <sup>1</sup> L L	Input Low Voltage  Input High Current  Input S		$V_{DDO} = 3.3V \pm 5\%, I_{OH} = -24mA$	2.6			V
V <sub>IH</sub> In V <sub>IL</sub> In I <sub>IH</sub> In I <sub>IL</sub> C V <sub>OH</sub> O	Output High Vol	tage;	$V_{DDO} = 2.5V \pm 5\%, I_{OH} = -12mA$	1.8			V
			$V_{DDO} = 1.8V \pm 0.2V, I_{OH} = -4mA$	V <sub>DDO</sub> - 0.3			V
I <sub>IH</sub> In Hi			$V_{DDO} = 3.3V \pm 5\%, I_{OL} = 24mA$			0.5	V
$V_{OL}$	Input High Volta Input Low Volta Input High Current Input Low Current  Output High Vol	age	$V_{DDO} = 2.5V \pm 5\%, I_{OL} = 12mA$			0.45	V
			$V_{DDO} = 1.8V \pm 0.2V, I_{OL} = 4mA$			0.35	V

#### **AC Electrical Characteristics**

**Table 5A. AC Characteristics,**  $V_{DD} = V_{DDO} = 3.3V \pm 5\%$ ,  $T_A = -40$ °C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f <sub>MAX</sub>	Output Frequency				250	MHz
tp <sub>LH</sub>	Propagation Delay, Low-to-High; NOTE 1		1.8	2.5	3.2	ns
tp <sub>HL</sub>	Propagation Delay, High-to-Low; NOTE 1		2.0	2.6	3.2	ns
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 2	155.52MHz, Integration Range: 12kHz – 20MHz		0.18		ps
tsk(i)	Input Skew; NOTE 3				145	ps
tsk(o)	Output Skew: NOTE 4				130	ps
tsk(pp)	Part-to-Part Skew; NOTE 3, 5				800	ps
t <sub>R</sub> / t <sub>F</sub>	Output Rise/Fall Time	20% to 80%	300		800	ps
odc	Output Duty Cycle	f <sub>OUT</sub> ≤ 175MHz	40		60	%
MUXISOLATION	MUX Isolation	100MHz		45		dB

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. Device will meet specifications after thermal equilibrium has been reached under these conditions.

- NOTE 1: Measured from V<sub>DD</sub>/2 of the input to V<sub>DDO</sub>/2 of the output.
- NOTE 2: Driving only one input clock.
- NOTE 3: This parameter is defined according with JEDEC Standard 65.
- NOTE 4: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at V<sub>DDO</sub>/2.
- NOTE 5: Defined as skew between outputs on different devices operating at the same supply voltage and with equal load conditions.
- Using the same type of inputs on each device, the outputs are measured at the differential cross points.

Table 5B. AC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f <sub>MAX</sub>	Output Frequency				250	MHz
tp <sub>LH</sub>	Propagation Delay, Low-to-High; NOTE 1		2.1	2.6	3.1	ns
tp <sub>HL</sub>	Propagation Delay, High-to-Low; NOTE 1		2.3	2.7	3.1	ns
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 2	155.52MHz, Integration Range: 12kHz – 20MHz		0.14		ps
tsk(i)	Input Skew; NOTE 3				100	ps
tsk(o)	Output Skew: NOTE 4				130	ps
tsk(pp)	Part-to-Part Skew; NOTE 3, 5				800	ps
t <sub>R</sub> / t <sub>F</sub>	Output Rise/Fall Time	20% to 80%	300		800	ps
odc	Output Duty Cycle		40		60	%
MUX <sub>ISOLATION</sub>	MUX Isolation	100MHz		45		dB

See notes in Table 5A above.

Table 5C. AC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $V_{DDO} = 1.8V \pm 0.2V$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f <sub>MAX</sub>	Output Frequency				250	MHz
tp <sub>LH</sub>	Propagation Delay, Low-to-High; NOTE 1		2.6	3.1	3.6	ns
tp <sub>HL</sub>	Propagation Delay, High-to-Low; NOTE 1		2.7	3.2	3.7	ns
fjit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 2	155.52MHz, Integration Range: 12kHz – 20MHz		0.16		ps
tsk(i)	Input Skew; NOTE 3				110	ps
tsk(o)	Output Skew: NOTE 4				130	ps
tsk(pp)	Part-to-Part Skew; NOTE 3, 5				800	ps
t <sub>R</sub> / t <sub>F</sub>	Output Rise/Fall Time	20% to 80%	450		850	ps
odc	Output Duty Cycle		40		60	%
MUXISOLATION	MUX Isolation	100MHz		45		dB

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. Device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Measured from  $V_{DD}/2$  of the input to  $V_{DDO}/2$  of the output.

NOTE 2: Driving only one input clock.

NOTE 3: This parameter is defined according with JEDEC Standard 65.

NOTE 4: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at V<sub>DDO</sub>/2.

NOTE 5: Defined as skew between outputs on different devices operating at the same supply voltage and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.

**Table 5D. AC Characteristics,**  $V_{DD} = V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40$ °C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f <sub>MAX</sub>	Output Frequency				250	MHz
tp <sub>LH</sub>	Propagation Delay, Low-to-High; NOTE 1		1.5	3.0	4.5	ns
tp <sub>HL</sub>	Propagation Delay, High-to-Low; NOTE 1		2.2	2.8	3.4	ns
fjit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 2	155.52MHz, Integration Range: 12kHz – 20MHz		0.22		ps
tsk(i)	Input Skew; NOTE 3				140	ps
tsk(o)	Output Skew: NOTE 4				125	ps
tsk(pp)	Part-to-Part Skew; NOTE 3, 5				800	ps
t <sub>R</sub> / t <sub>F</sub>	Output Rise/Fall Time	20% to 80%	300		700	ps
odc	Output Duty Cycle	f <sub>OUT</sub> ≤ 175MHz	40		60	%
MUXISOLATION	MUX Isolation	100MHz		45		dB

See notes in Table 5C above.

Table 5E. AC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $V_{DDO} = 1.8V \pm 0.2V$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f <sub>MAX</sub>	Output Frequency				250	MHz
tp <sub>LH</sub>	Propagation Delay, Low-to-High; NOTE 1		2.2	3.2	4.2	ns
tp <sub>HL</sub>	Propagation Delay, High-to-Low; NOTE 1		2.2	3.2	4.0	ns
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 2	155.52MHz, Integration Range: 12kHz – 20MHz		0.19		ps
tsk(i)	Input Skew; NOTE 3				110	ps
tsk(o)	Output Skew: NOTE 4				125	ps
tsk(pp)	Part-to-Part Skew; NOTE 3, 5				800	ps
t <sub>R</sub> / t <sub>F</sub>	Output Rise/Fall Time	20% to 80%	450		850	ps
odc	Output Duty Cycle	f <sub>OUT</sub> ≤ 200MHz	40		60	%
MUX <sub>ISOLATION</sub>	MUX Isolation	100MHz		45		dB

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. Device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Measured from  $V_{DD}/2$  of the input to  $V_{DDO}/2$  of the output.

NOTE 2: Driving only one input clock.

NOTE 3: This parameter is defined according with JEDEC Standard 65.

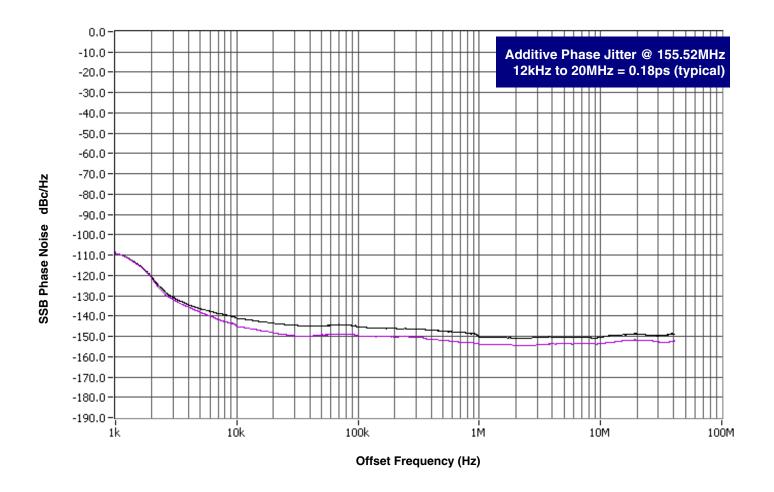
NOTE 4: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at V<sub>DDO</sub>/2.

NOTE 5: Defined as skew between outputs on different devices operating at the same supply voltage and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.

#### **Additive Phase Jitter**

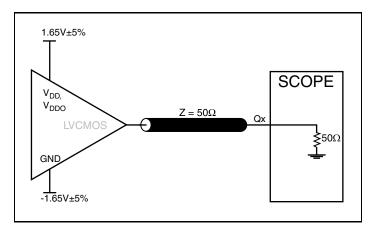
The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the *dBc Phase Noise*. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio of the power in the 1Hz band

to the power in the fundamental. When the required offset is specified, the phase noise is called a *dBc* value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.

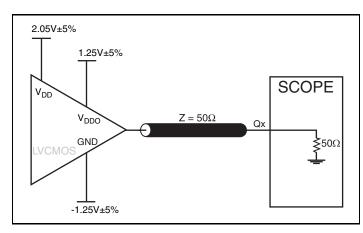


As with most timing specifications, phase noise measurements has issues relating to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device. This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.

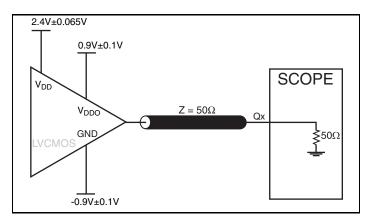
### **Parameter Measurement Information**



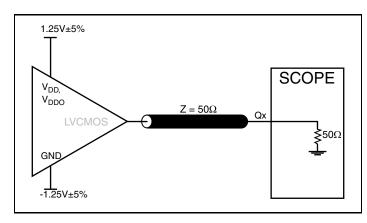
3.3V Output Load AC Test Circuit



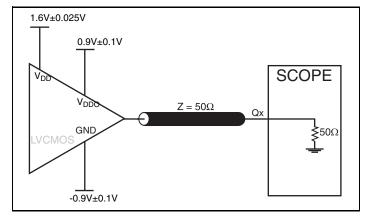
3.3V Core/2.5V Output Load AC Test Circuit



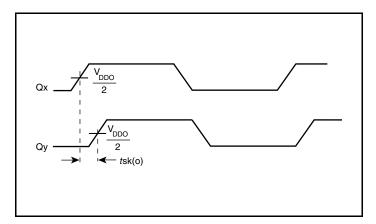
3.3V Core/1.8V Output Load AC Test Circuit



2.5V Core/2.5V Output Load AC Test Circuit

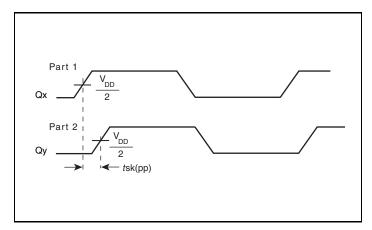


2.5V Core/1.8V Output Load AC Test Circuit



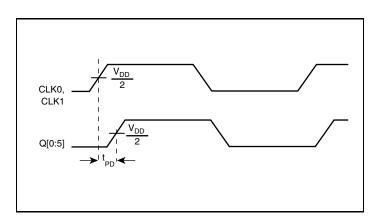
**Output Skew** 

# **Parameter Measurement Information, continued**

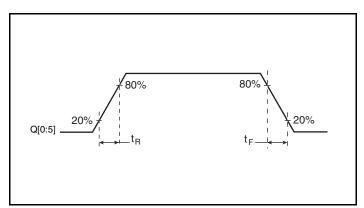


Q[0:5]  $\frac{V_{DDO}}{2}$   $odc = \frac{t_{PW}}{t_{PERIOD}} \times 100\%$ 

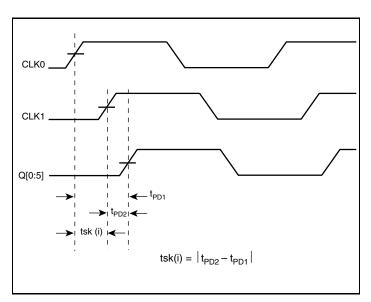
**Part-to-Part Skew** 



**Output Duty Cycle/Pulse Width/Period** 



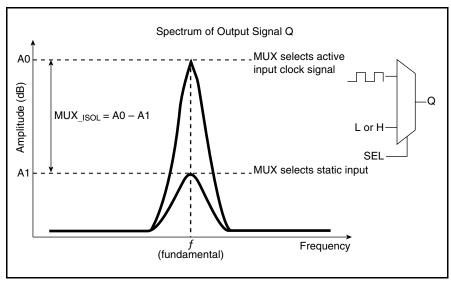
**Propagation Delay** 



**Output Rise/Fall Time** 

**Input Skew** 

# **Parameter Measurement Information, continued**



**MUX** Isolation

# **Application Information**

### **Recommendations for Unused Input and Output Pins**

### Inputs:

#### **CLK Inputs**

For applications not requiring the use of a clock input, it can be left floating. Though not required, but for additional protection, a  $1 k\Omega$  resistor can be tied from the CLK input to ground.

#### **LVCMOS Control Pins**

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A  $1k\Omega$  resistor can be used.

### **Outputs:**

#### **LVCMOS Outputs**

All unused LVCMOS output can be left floating. There should be no trace attached.

# **Reliability Information**

Table 6.  $\theta_{\text{JA}}$  vs. Air Flow Table for a 20 Lead TSSOP

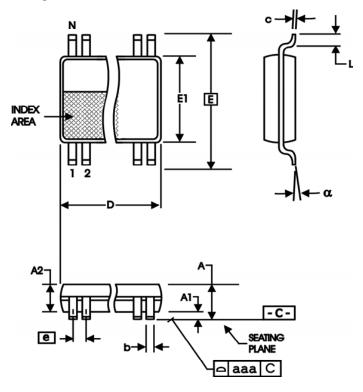
$\theta_{JA}$ vs. Air Flow				
Meters per Second	0	1	2.5	
Multi-Layer PCB, JEDEC Standard Test Boards	91.1°C/W	86.7°C/W	84.6°C/W	

#### **Transistor Count**

The transistor count for ICS83056I-01 is: 967

# **Package Outline and Package Dimensions**

Package Outline - G Suffix for 20 Lead TSSOP



**Table 7. Package Dimensions** 

All Dimensions in Millimeters				
Symbol	Minimum Maximum			
N	20			
Α		1.20		
<b>A</b> 1	0.05	0.15		
A2	0.80	1.05		
b	0.19	0.30		
С	0.09	0.20		
D	6.40	6.60		
E	6.40 Basic			
E1	4.30	4.50		
е	0.65 Basic			
L	0.45	0.75		
α	0°	8°		
aaa		0.10		

Reference Document: JEDEC Publication 95, MO-153

# **Ordering Information**

#### **Table 9. Ordering Information**

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
83056AGI-01	ICS83056AI01	20 Lead TSSOP	Tube	-40°C to 85°C
83056AGI-01T	ICS83056AI01	20 Lead TSSOP	2500 Tape & Reel	-40°C to 85°C
83056AGI-01LF	ICS3056AI01L	"Lead-Free" 20 Lead TSSOP	Tube	-40°C to 85°C
83056AGI-01LFT	ICS3056AI01L	"Lead-Free" 20 Lead TSSOP	2500 Tape & Reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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### **Contact Information:**

www.IDT.com

#### Sales

800-345-7015 (inside USA) +408-284-8200 (outside USA) Fax: 408-284-2775 www.IDT.com/go/contactIDT

#### **Technical Support**

netcom@idt.com +480-763-2056

#### **Corporate Headquarters**

Integrated Device Technology, Inc. 6024 Silver Creek Valley Road San Jose, CA 95138 United States 800-345-7015 (inside USA) +408-284-8200 (outside USA)

